PCN Number:		202	10326	5004.2						PCN D	ate:	Mar 29 2021	
Title: Qualification of new Fab site (CFAB) using qualified Process Technology, Die Revision Probe site, and additional Assembly site/BOM options for select devices							, Die Revision,						
Cust	tomer	Conta	ct:	PCN A	Nanager	-	Dept:		Quality S	Service	es		
Proposed 1st Ship Date: Sep 2			Sep 2	25 2	021	Estimated Sample Date provided Availability: Sample reques			•				
Chai	Change Type:												
	Assemb	oly Sit	e			\boxtimes	✓ Design		Wafe	r Bum	p Site		
	Assemb	oly Pro	cess				Data Sheet Wafer Bump Materia			p Material			
Assembly Materials				Part nu	ımber	change		Wafe	r Bum	p Process			
Mechanical Specification				Test Si	te			Wafe	r Fab S	Site			
Packing/Shipping/Labeling				Test Pr	ocess		\boxtimes	Wafe	r Fab I	Materials			
							\boxtimes	Wafe	r Fab I	Process			
	PCN Details												

Description of Change:

Texas Instruments is pleased to announce the qualification of a new fab & process technology, (CFAB, JI3), die revisions, probe site, and AT (FMX) site/BOM (MLA) options for selected devices as listed below in the product affected section. Construction differences are noted below:

С	urrent Fab Site	9	Additional Fab Site		
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter
SFAB	JI1	150 mm	CFAB	JI3	200 mm

The die was also changed as a result of the process change.

Probe site change:

	Current:	New:
Probe Site	D-Lin	None

Construction differences are noted below:

Group 1 CFAB/Process migration & updated BOM in FMX for D Devices:

	Current - FMX	New - FMX
Lead finish/prep	NiPdAu, Non RLF or RLF	NiPdAu, RLF
Bond wire diameter	Au, 0.96 or Cu, 0.96 mils	Cu, 0.80 mils
Mold Compound	4205694 or 4211880	4211880
MSL	L3/260C or L1/260C	L1/260C

Group 2 CFAB/Process migration & FMX as additional AT site from MLA for D Devices:

	Current - MLA	New - FMX
Mount Compound	4208458	4147858
Mold Compound	4209640	4211880
Lead finish	NiPdAu, non RLF	NiPdAu, RLF
Bond wire diameter	Au, 0.96 mils	Cu, 0.80 mils

Group 3 CFAB/Process migration & FMX as additional AT site from TAI for D Devices:

	Current - TAI	New - FMX
Mount Compound	4042500	4147858
Mold Compound	4205694	4211880
Lead finish	NiPdAu, non RLF	NiPdAu, RLF
Bond wire diameter	Au, 0.96 mils	Cu, 0.80 mils

Group 4 CFAB/Process migration & updated BOM in MLA for PW Devices:

	MLA - Current	MLA - New
Bond wire diameter	Au, 0.96 mils or Cu, 1.0 mils	Cu, 0.80 mils

Test coverage, insertions, conditions will remain consistent with current testing and verified with test MQ.

Reason for Change:

These changes are part of our multiyear plan to transition products from our 150-milimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Anticipated impact on Material Declaration

			l
Ш	No Impact to the	\bowtie	Material Declarations or Product Content reports are driven
	Material Declaration		from production data and will be available following the
			production release. Upon production release the revised
			reports can be obtained at the site link below
			http://www.ti.com/quality/docs/materialcontentsearch.tsp

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
SH-BIP-1	SHE	USA	Sherman
CFAB	CU3	CHN	Chengdu

Die Rev:

Current	New	
Die Rev [2P]		Die Rev [2P]
		•

Assembly Site Information:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
TAI	TAI	TWN	Chung Ho, New Taipei City
MLA	MLA	MYS	Kuala Lumpur
FMX	MEX	MEX	Aguascalientes

Sample product shipping label (not actual product label)



LBL: 5A (L)TO:1750



(1P) SN74LS07NSR (D) 0336 (a) 2000 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483SI2 (P) (2P) REV: (2P) REV: (V) 0033317 (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) ACO: MYS

Product Affected:

Group 1 Device list: CFAB/Process migration & updated BOM in FMX for D Devices:

LM158AQDRDL	LM2904DRCT	LM2904QDRSV	LM2904VQDRQ1
LM2904AVQDR	LM2904QDRDL	LM2904VQDR	MLA00339DRG4
LM2904AVQDRG4	LM2904QDRG4Q1	LM2904VQDRG4	SN102755DR
LM2904AVQDRG4Q1	LM2904QDRQ1	LM2904VQDRG4Q1	SN104630DR
LM2904AVQDRQ1			

Group 2 Device list: CFAB/Process migration & FMX as additional AT site from MLA for D Devices:

MLA00312DR	LBT-LM2904DR	LM2904VZQDRQ1

Group 3 Device list: CFAB/Process migration & FMX as additional AT site from TAI for D Devices:

LM2904QDR

Group 4 Device list: CFAB/Process migration & updated BOM in MLA for PW Devices:

LM2904AVQPWR	LM2904AVQPWRQ1	LM2904QPWRQ1	LM2904VQPWRG4Q1
LM2904AVQPWRCT	LM2904AVQPWRRB	LM2904VQPWR	LM2904VQPWRKN
LM2904AVQPWRG4	LM2904AVQPWRRBG4	LM2904VQPWRCT	LM2904VQPWRQ1
LM2904AVQPWRG4Q1	LM2904QPWRG4Q1	LM2904VQPWRG4	MLA00415PWR

Group 1, 2, & 3 (SOIC Devices) Qual report:



TI Information Selective Disclosure

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Approved 16-Mar-2021

Product Attributes

Attributes	Qual Device: LM2904BQDRQ1	QBS Product Reference: <u>LM2904BQDRQ1</u>	QBS Package Reference: <u>LM2903BQDRQ1</u>
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range	-40 to +125 C	-40 to +125 C	-40 to +85 C
Product Function	Signal Chain	Signal Chain	Signal Chain
Wafer Fab Supplier	CFAB	CFAB	CFAB
Die Revision	2.0	2.0	A0
Assembly Site	FMX	FMX	FMX
Package Type	SOIC	SOIC	SOIC
Package Designator	D	D	D
Ball/Lead Count	8	8	8

⁻ QBS: Qual By Similarity

⁻ Qual Device LM2904BQDRQ1 is qualified at LEVEL1-260C

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LM2904BQDRQ1	QBS Product Reference: LM2904BQDRQ1	QBS Package Reference: LM2903BQDRQ1
		Test Group A	– Accelera	ted Envir	onment Stress Tests				
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Automotive Preconditioning Level 1	Level 1- 260C	1/78/0	-	-
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Automotive Preconditioning Level 2	Level 2- 260C	-	3/1499/10 (1)	-
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	-	3/231/0	-
AC	А3	JEDEC JESD22-A102	3	77	Autoclave 121C	96 Hours	1/77/0	-	-
UHAST	А3	JEDEC JESD22-A118	3	77	Unbiased HAST 130C/85%RH	96 Hours	-	3/231/0	-
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	1/77/0	3/231/0	-
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	-	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp Storage Bake 175C	500 Hours	-	3/135/0	-
		Test Group B	 Accelera 	ited Lifetii	me Simulation Tests				
HTOL	B1	JEDEC JESD22-AA108	3	77	Auto High Temp Operating Life Grade 1, 150C	408 Hours	-	3/231/0	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 Hours	-	3/2400/4 (1)	-
EDR	В3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	-	-
		Test Group	C – Packa	ge Assem	bly Integrity Tests				
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear (Cpk>1.67)	Wires	-	3/90/0	-
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull (Cpk>1.67)	Wires	-	3/90/0	-
SD	СЗ	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb	-	1/15/0	-
SD	СЗ	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb-free	-	1/15/0	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Auto Physical Dimensions	Cpk>1.67	-	3/30/0	-

		Test Grou	p D -	- Die					
Е	M D	1 JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	-	-
TD	DB D	2 JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	-	-
Н	CI D	3 JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	-	-
NE	BTI D	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	-	-
S	M D		-	-	Stress Migration	-	Completed Per Process Technology Requirements	-	-
		Test Gro							
HE	BM E	2 AEC Q100-002	1	3	ESD - HBM - Q100	2000 V	-	3/9/0	-
CE	M E	3 AEC Q100-011	1	3	ESD - CDM - Q100	1500 V	-	3/9/0	-
L	U E	4 AEC Q100-004	1	6	Latch-up	Per AEC-Q100- 004	-	3/18/0	-
E	D E	5 AEC Q100-009	3	30	Auto Electrical Distributions	Cpk>1.67	-	3/90/0	-
				Add					
M	SL -	Moisture Sensitivity Level	1	12	Automotive Moist Sens. L1	Level 1-260C	1/12/0	-	3/36/0
Ms	SL -	Moisture Sensitivity Level	1	12	Automotive Moist Sens. L2	Level 2-260C	-	3/36/0	-

A1 (PC): Preconditioning: Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40° C to $+150^{\circ}$ C Grade 1 (or Q): -40° C to $+125^{\circ}$ C Grade 2 (or T): -40° C to $+105^{\circ}$ C Grade 3 (or I): -40° C to $+85^{\circ}$ C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Green/Pb-free Status:
Qualified Pb-Free(SMT) and Green
Note (1): Precon and ELFR fails due to a defect screenable at production test.

Group 4 (PW Devices) Qual report:



TI Information Selective Disclosure

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Approved 28-Jul-2020

Product Attributes

Attributes	Qual Device: LM2904BQPWRQ1	QBS Product Function / Package Reference: <u>LM2903BQPWRQ1</u>	QBS Process Reference: <u>LM2904BQDRQ1</u>
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range	-40 to +125 C	-40 to +125 C	-40 to +125 C
Product Function	Signal Chain	Signal Chain	Signal Chain
Wafer Fab Supplier	CFAB	CFAB	CFAB
Die Revision	С	1.0	2.0
Assembly Site	MLA	MLA	FMX
Package Type	TSSOP	TSSOP	SOIC
Package Designator	PW	PW	D
Ball/Lead Count	8	8	8

⁻ QBS: Qual By Similarity

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

	Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LM2904BQPWRQ1	QBS Product Function / Package Reference: <u>LM2903BQPWRQ1</u>	QBS Process Reference: LM2904BQDRQ1
			Test Group A –	Acceler	ated Envii	ronment Stress Tests				
	PC	A1	JEDEC J-STD- 020 JESD22-A113	3	77	Automotive Preconditioning Level 1	Level 1- 260C	1/479/0	12/1275/2 (1)	-
	PC	A1	JEDEC J-STD- 020 JESD22-A113	3	77	Automotive Preconditioning Level 2	Level 2- 260C	-	-	3/1499/10 (3)
	HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST, 130C/85%RH	96 Hours	1/77/0	3/231/0	3/231/0
	AC	A3	JEDEC JESD22- A102	3	77	Autoclave 121C	96 Hours	1/77/0	-	-
ı	JHAST			-	-	Unbiased HAST 130C/85%RH	96 Hours	-	3/231/0	3/231/0
	TC	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle, - 65/150C	500 Cycles	1/77/0	3/231/2 (2)	3/231/0
	TC-BP	A4	MIL-STD883 Method 2011	1	60	Post TC Bond Pull	Wires	1/30/0	-	-
	PTC	A5	JEDEC JESD22- A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	-	-
	HTSL	A6	JEDEC JESD22- A103	1	45	High Temp Storage Bake 175C	500 Hours	1/45/0	-	3/135/0
	HTSL	A6	JEDEC JESD22- A103	1	45	High Temp Storage Bake 175C	500 Hours	-	3/231/0	-
			Test Group B -	Acceler	ated Lifet	ime Simulation Tests				
	HTOL	B1	JEDEC JESD22- A108	3	77	Life Test, 150C	300 Hours	-	3/231/0	-
	HTOL	B1	JEDEC JESD22- A108	3	77	Life Test, 150C	408 Hours	1/77/0	-	3/231/0
	ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 Hours	-	-	3/2400/4 (3)
	EDR	В3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	-	-

⁻ Qual Device LM2904BQPWRQ1 is qualified at LEVEL1-260C

Test Group C – Package Assembly Integrity Tests										
w	BS (C1	AEC Q100-001	1	30	Wire Bond Shear (Cpk>1.67)	Wires	1/30/0	-	3/90/0
W	BP (C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull (Cpk>1.67)	Wires	1/30/0	-	3/90/0
5	SD (СЗ	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb	1/15/0	-	1/15/0
5	SD (СЗ	JEDEC JESD22-B102	1	15	Surface Mount Solderability	Pb-free	1/15/0	-	1/15/0
F	PD (C4	JEDEC JESD22-B100 and B108	3	10	Auto Physical Dimensions	Cpk>1.67	3/30/0	-	3/30/0
	LI	C6	JEDEC JESD22-B105	1	50	Lead Pull to Destruction	Leads	1/24/0	-	-
	Test Group D – Die Fabrication Reliability Tests									
E	EM I	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	-	-
TC	DDB I	D2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	-	-
Н	ICI I	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	-	-
N	вті і	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	-	-
S	SM I	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	-	-
			Test Group	E – I	Electi	ical Verification Tests				
Н	BM I	E2	AEC Q100-002	1	3	ESD - HBM - Q100	2000 V	1/3/0	3/9/0	3/9/0
CI	DM I	E3	AEC Q100-011	1	3	ESD - CDM - Q100	1500 V	1/3/0	3/9/0	3/9/0
L	.U I	E4	AEC Q100-004	1	6	Latch-up	Per AEC-Q100- 004	1/6/0	3/18/0	3/18/0
E	D I	E5	AEC Q100-009	3	30	Auto Electrical Distributions	Cpk>1.67	3/90/0	-	3/90/0
				Ad	ditio	nal Tests				
M	ISL			-	12	Automotive Moist Sens. L1	Level 1-260C	1/12/0	-	-
M	ISL			-	12	Automotive Moist Sens. L2	Level 2-260C	-	-	3/36/0

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED

Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Green/Ph-free Status:

Qualified Pb-Free(SMT) and Green

Note (1): Two units damaged due to mishandling at test. Discounted.

Note (2): Two units damaged in handler at test. Discounted.

Note (3): Precon and ELFR fails due to a defect screenable at production test.

or questions regarding this notice, e-mails can be sent to the contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
WW PCN Team	PCN_ww_admin_team@list.ti.com

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL

WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale (www.ti.com/legal/termsofsale.html) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.